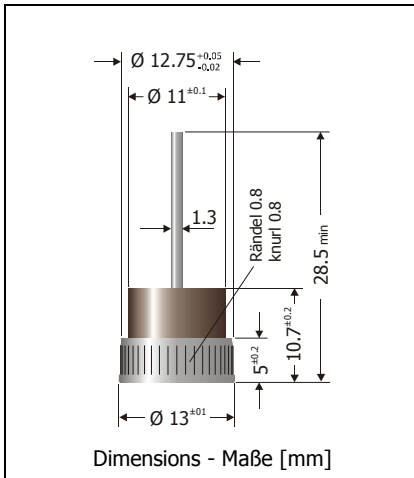


BYP35A05 ... BYP35A6, BYP35K05 ... BYP35K6

**Silicon-Press-Fit-Diodes – High Temperature Diodes
Silizium-Einpress-Dioden – Hochtemperatur-Dioden**

Version 2011-11-18



Nominal Current 35 A
 Nennstrom

Repetitive peak reverse voltage 50 ... 600 V
 Periodische Spitzensperrspannung

Metal press-fit case with plastic cover
 Metall-Einpressgehäuse mit Plastik-Abdeckung

Weight approx. 10 g
 Gewicht ca.

Compound has classification UL94V-0
 Vergussmasse nach UL94V-0 klassifiziert

Standard packaging: bulk
 Standard Lieferform: lose im Karton



Maximum ratings

Grenzwerte

Type / Typ Wire to / Draht an		Repetive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V]	Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V]
Anode	Cathode		
BYP35A05	BYP35K05	50	60
BYP35A1	BYP35K1	100	120
BYP35A2	BYP35K2	200	240
BYP35A3	BYP35K3	300	360
BYP35A4	BYP35K4	400	480
BYP35A6	BYP35K6	600	700

Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last	$T_C = 150^\circ\text{C}$	I_{FAV}	35 A
Repetitive peak forward current Periodischer Spitzenstrom	$f > 15\text{ Hz}$	I_{FRM}	130 A ¹⁾
Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwellen	$T_A = 25^\circ\text{C}$	I_{FSM}	360/400 A
Rating for fusing, $t < 10\text{ ms}$ Grenzlastintegral, $t < 10\text{ ms}$	$T_A = 25^\circ\text{C}$	i^2t	660 A ² s
Operating junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_s	-50...+215°C -50...+215°C

1 Max. case temperature $T_C = 150^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 150^\circ\text{C}$

Characteristics
Kennwerte

Forward Voltage – Durchlass-Spannung	$T_j = 25^\circ\text{C}$ $I_F = 35\text{ A}$	V_F	< 1.1 V
Leakage Current – Sperrstrom	$T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$	I_R	< 100 μA
Thermal Resistance Junction – Case Wärmewiderstand Sperrschicht – Gehäuse		R_{thC}	< 0.8 K/W
Maximum pressing force Maximaler Einpressdruck		F_{pmax}	7 kN

